



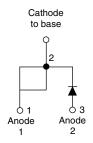
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 8 A



TO-247AC modified



PRODUCT SUMMARY	
Package	TO-247AC modified (2 pins)
I _{F(AV)}	8 A
V_{R}	1200 V
V _F at I _F	3.3 V
t _{rr} typ.	28 ns
T _J max.	150 °C
Diode variation	Single die

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC-JESD47
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V_{R}		1200	V				
Maximum continuous forward current	I _F	T _C = 100 °C	8					
Single pulse forward current	I _{FSM}		130	Α				
Maximum repetitive forward current	I _{FRM}		32					
Maniana	_	T _C = 25 °C	73.5	14/				
Maximum power dissipation	P_{D}	T _C = 100 °C	29	W				
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C				



VS-HFA08PB120PbF, VS-HFA08PB120-N3

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage		I _F = 8.0 A		-	2.6	3.3	V		
	V _{FM}	I _F = 16 A	See fig. 1	-	3.4	4.3			
		I _F = 8.0 A, T _J = 125 °C		-	2.4	3.1			
Maximum reverse		V _R = V _R rated	Coo fig. 0	-	0.31	10	μА		
leakage current	I _{RM}	T _J = 125 °C, V _R = 0.8 x V _R rated	See fig. 2	-	135	1000			
Junction capacitance	C _T	V _R = 200 V See fig. 3		-	11	20	pF		
Series inductance	L _S	Measured lead to lead 5 mm from page 1	ackage body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5, 10	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	0 A/μs, V _R = 30 V	-	28	-			
	t _{rr1}	T _J = 25 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	63	95	ns		
	t _{rr2}	T _J = 125 °C		-	106	160			
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	- A		
	I _{RRM2}	T _J = 125 °C		-	6.2	11			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	140	380			
See fig. 7	Q _{rr2}	T _J = 125 °C		-	335	880	nC		
Peak rate of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	-			
	dl _{(rec)M} /dt2	T _J = 125 °C		-	85	-	A/µs		

THERMAL - MECHAN	THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.7					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased		0.25						
Weight			-	6.0	-	g				
vveignt			-	0.21	-	OZ.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC modified (JEDEC)	HFA08PB120							

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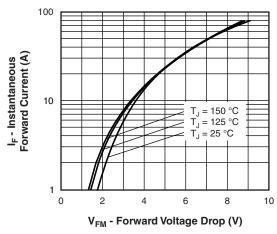


Fig. 1 - Maximum Forward Voltage Drop Characteristics

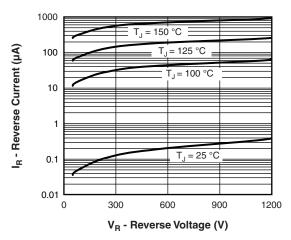


Fig. 2 - Values of Reverse Current vs. Reverse Voltage

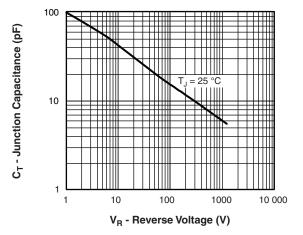


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

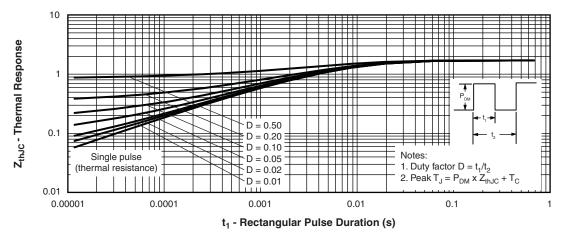


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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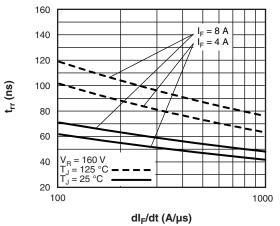


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

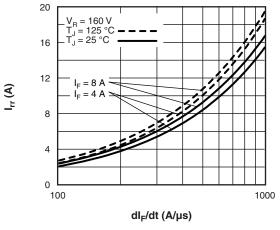


Fig. 6 - Typical Recovery Current vs. dl_F/dt

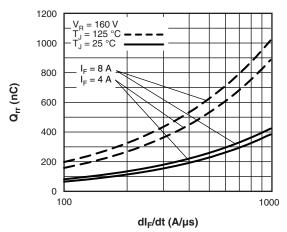


Fig. 7 - Typical Stored Charge vs. dl_F/dt

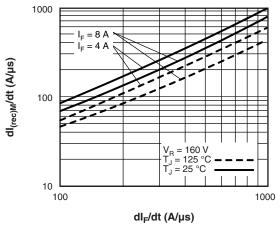


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

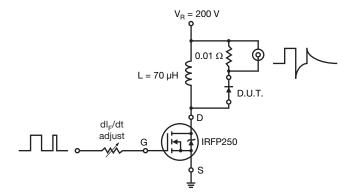
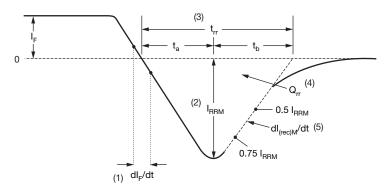


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA08PB120PbF, VS-HFA08PB120-N3

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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{BBM}

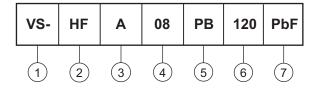
$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

Current rating (08 = 8A)

5 - PB = TO-247AC modified

Voltage rating: (120 = 1200 V)

7 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-HFA08Pb120PbF	25	500	Antistatic plastic tube							
VS-HFA08Pb120-N3	25	500	Antistatic plastic tube							

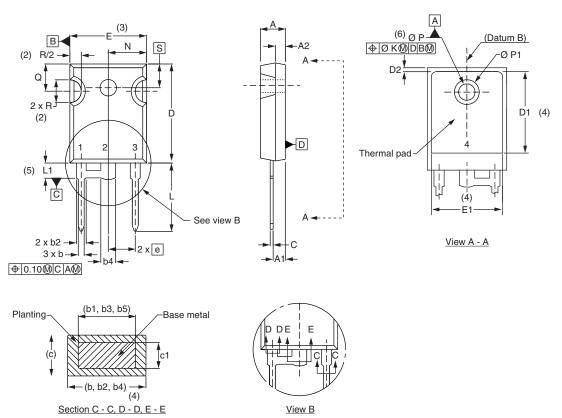
LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95541						
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255						
	TO-247AC modified -N3	www.vishay.com/doc?95442						



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TO-247 modified

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		NCHES NOTE		INCHES		NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053			
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3		
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-			
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC			
b1	0.99	1.35	0.039	0.053			ØK	0.2	254	0.0	010			
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634			
b3	1.65	2.33	0.065	0.092			L1	3.71	4.29	0.146	0.169			
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3			
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144			
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291			
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224			
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216			
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	' BSC			

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



Legal Disclaimer Notice

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